

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	109958	semiconductor and (dice cicing separation separat\$3 cutting cut\$2 dividing divid\$3 singularity) with (wafer substrate workpiece)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/07 07:49
L3	109977	semiconductor and ((dice cicing separation separat\$3 cutting cut\$2 dividing divid\$3 singularity) with (wafer substrate workpiece))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/07 07:57
L4	27786	3 and ((dice cicing separation separat\$3 cutting cut\$2 dividing divid\$3 singularity) with (line groove alignment adj mark))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/07 07:52
L5	14959	4 and (((front back upper lower first second opposit\$3) near\$5 (side surface)) with (wafer substrate workpiece))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/07 08:25
L6	112461	semiconductor and ((dice dicing separation separat\$3 cutting cut\$2 dividing divid\$3 singularity) with (wafer substrate workpiece))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/07 08:00
L7	53705	6 and (((front back upper lower first second opposit\$3) near\$5 (side surface)) with (wafer substrate workpiece))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/07 07:57
L8	1753	7 and ((dice dicing separation separat\$3 cutting cut\$2 dividing divid\$3 singularity) with (laser near\$5 beam))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/07 07:59
L9	1050	8 and ((individual single) with (wafer substrate workpiece))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/07 08:02
L10	5	9 and ((parting adj line) with (wafer substrate workpiece))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/07 08:03

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L7	129251	semiconductor and ((dice dicing separation separat\$3 cutting cut\$2 dividing divid\$3 singularity individual single) near5 (wafer substrate workpiece))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/07 08:29
L16	24785	7 and ((dice dicing separation separat\$3 cutting cut\$2 dividing divid\$3 singularity single) near5 (line groove alignment adj mark))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/07 08:38
L17	1142	16 and ((dice dicing separation separat\$3 cutting cut\$2 dividing divid\$3 singularity singleline groove alignment adj mark) near5 (polish\$3 blast\$5))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/07 08:42
L18	1530	16 and ((dice dicing separation separat\$3 cutting cut\$2 dividing divid\$3 singularity single line groove alignment adj mark) near5 (polish\$3 blast\$5))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/07 08:41
L19	67	18 and ((dice dicing separation separat\$3 cutting cut\$2 dividing divid\$3 singularity singleline groove alignment adj mark) near5 (laser near5 beam))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/07 08:42

L11	53705	6 and (((front back upper lower first second opposit\$3) near5 (side surface)) with (wafer substrate workpiece))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/07 08:25
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